

SKM400GB12E4



SEMITRANS® 3

IGBT4 Modules

SKM400GB12E4

Features

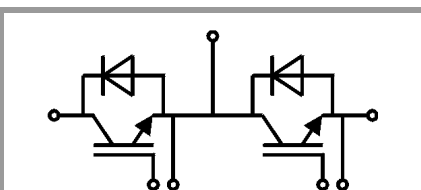
- IGBT4 = 4. Generation (Trench)IGBT
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_{CNOM}$
- Soft switching 4. Generation CAL diode (CAL4)
- UL recognized, file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders at f_{sw} up to 20 kHz

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ\text{C}$



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Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	1200	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	616
		$T_c = 80^\circ\text{C}$	474
I_{Cnom}		400	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	1200	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10
	$V_{GE} \leq 15\text{ V}$		
	$V_{CES} \leq 1200\text{ V}$		μs
T_j		-40 ... 175	$^\circ\text{C}$
Inverse diode			
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	440
		$T_c = 80^\circ\text{C}$	329
I_{Fnom}		400	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$	1200	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	1980	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	80°C	500	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, $t = 1\text{ min}$	4000	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
IGBT					
$V_{CE(sat)}$	$I_C = 400\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.80	2.05	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	2.50	2.88	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	3.75	4.00	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 15.2\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	24.6		nF
C_{oes}		$f = 1\text{ MHz}$	1.62		nF
C_{res}		$f = 1\text{ MHz}$	1.38		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		2260		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		1.9		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 400\text{ A}$	$T_j = 150^\circ\text{C}$	242		ns
t_r	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	47		ns
E_{on}	$R_{Gon} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	33		mJ
$t_{d(off)}$	$R_{Goff} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	580		ns
t_f	$di/dt_{on} = 9700\text{ A}/\mu\text{s}$ $di/dt_{off} = 4300\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	101		ns
E_{off}		$T_j = 150^\circ\text{C}$	56		mJ
$R_{th(j-c)}$	per IGBT			0.072	K/W



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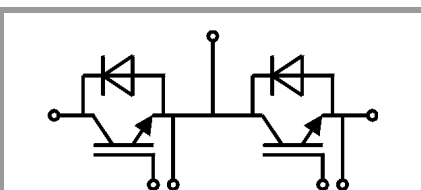
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 400 \text{ A}$ $V_{GE} = 0 \text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.20	2.52	V
		$T_j = 150^\circ\text{C}$		2.15	2.47	V
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		2.3	2.5	m Ω
		$T_j = 150^\circ\text{C}$		3.1	3.4	m Ω
I_{RRM}	$I_F = 400 \text{ A}$	$T_j = 150^\circ\text{C}$		450		A
Q_{rr}	$di/dt_{off} = 8800 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		68		μC
E_{rr}	$V_{GE} = \pm 15 \text{ V}$ $V_{CC} = 600 \text{ V}$	$T_j = 150^\circ\text{C}$		30.5		mJ
$R_{th(j-c)}$	per diode				0.14	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.25		m Ω
		$T_c = 125^\circ\text{C}$		0.5		m Ω
$R_{th(c-s)}$	per module			0.02	0.038	K/W
M_s	to heat sink M6		3		5	Nm
M_t		to terminals M6	2.5		5	Nm
						Nm
w					325	g



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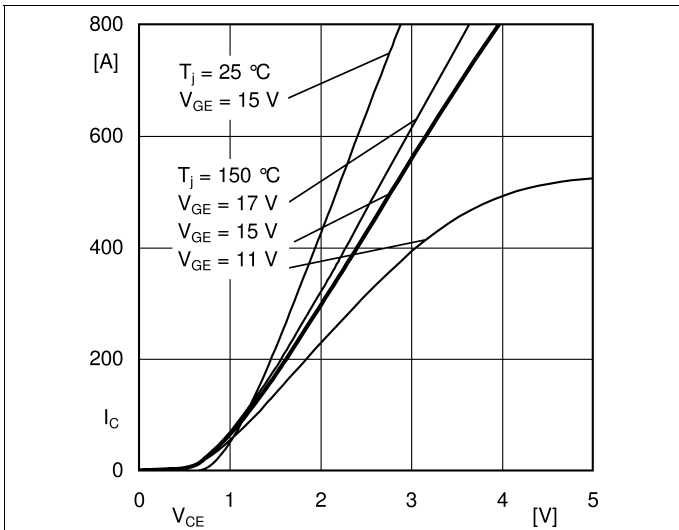


Fig. 1: Typ. output characteristic, inclusive R_{CC+EE}

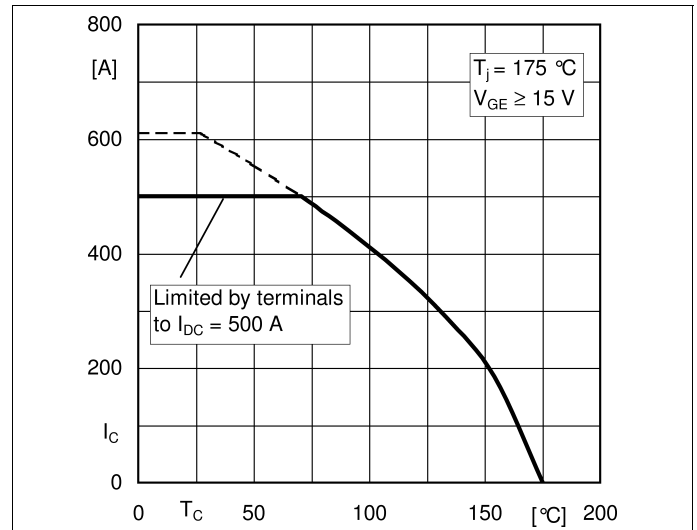


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

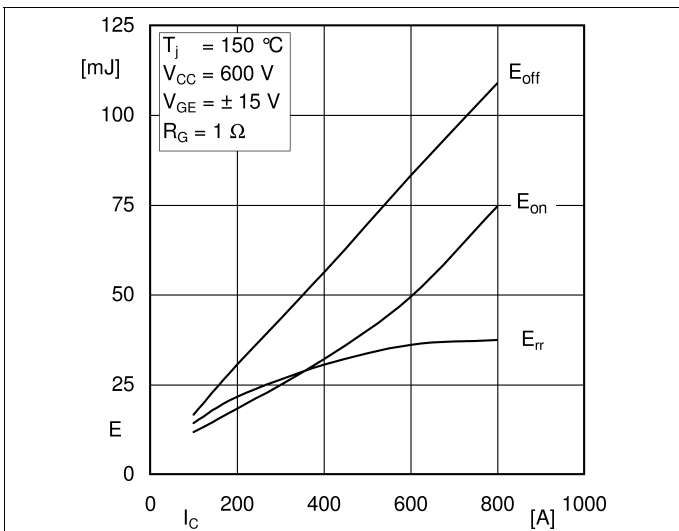


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

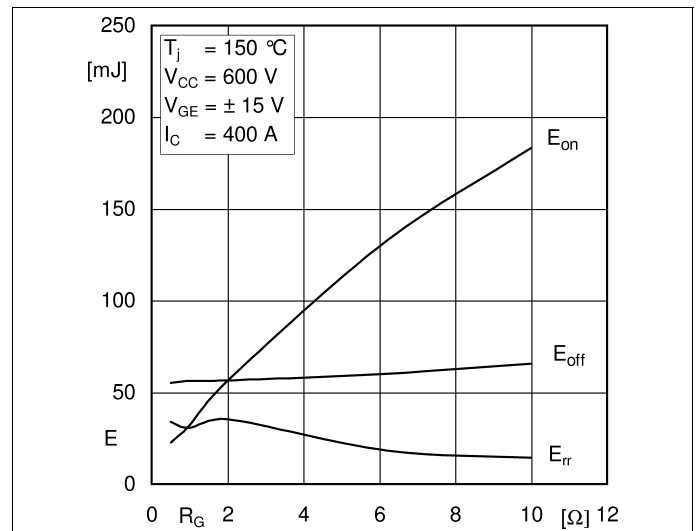


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

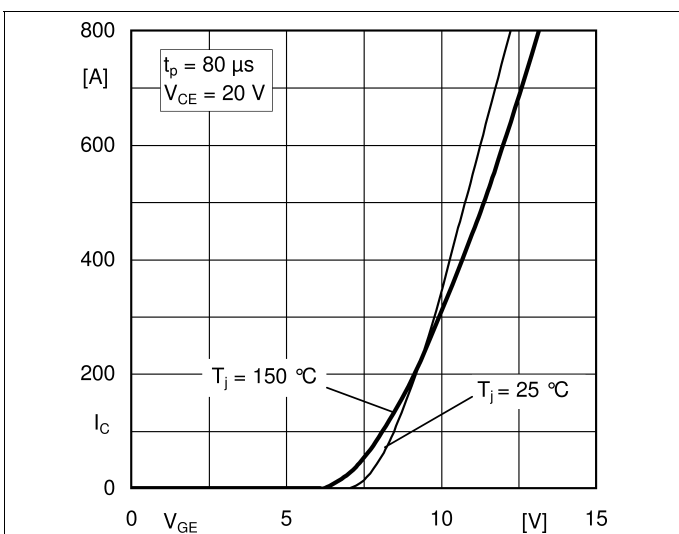


Fig. 5: Typ. transfer characteristic

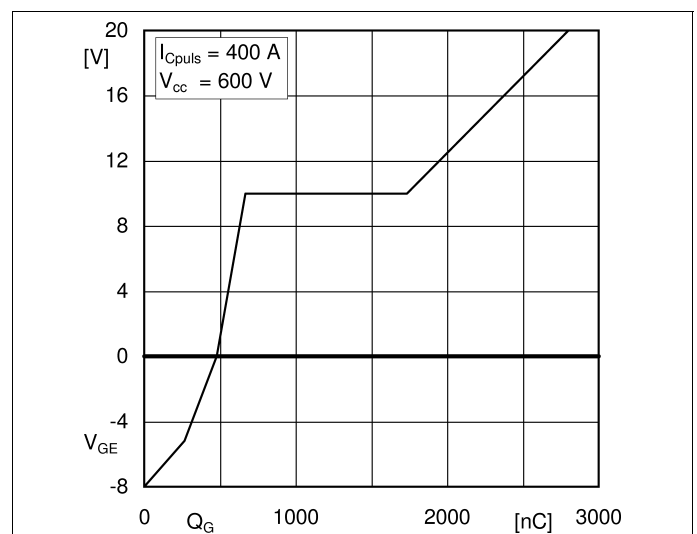
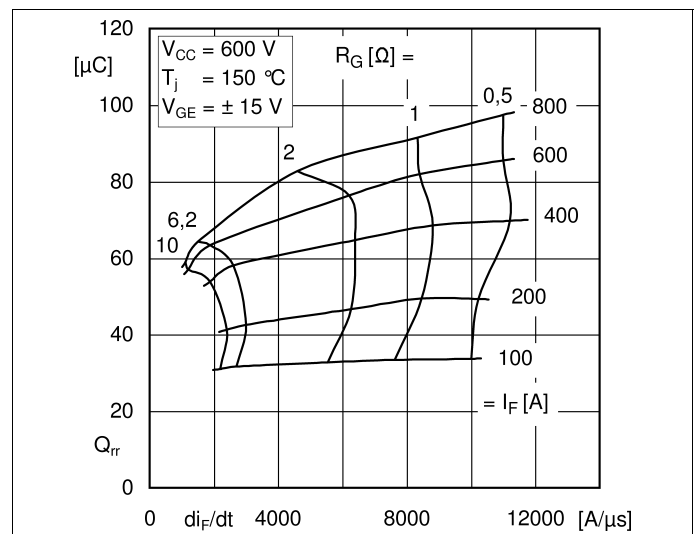
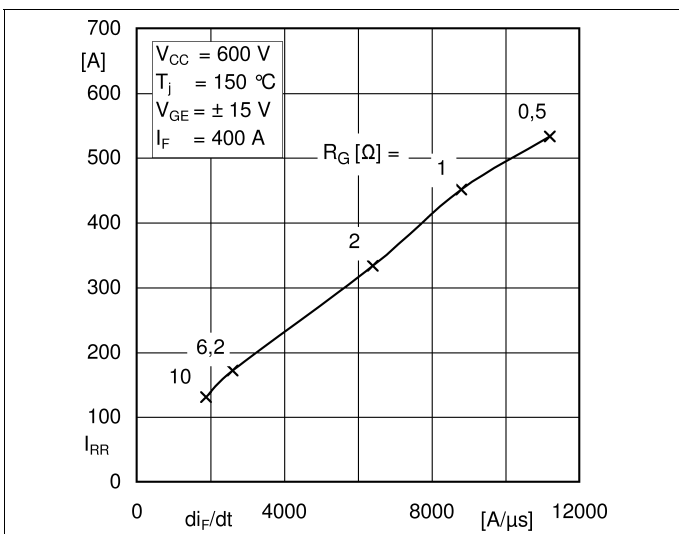
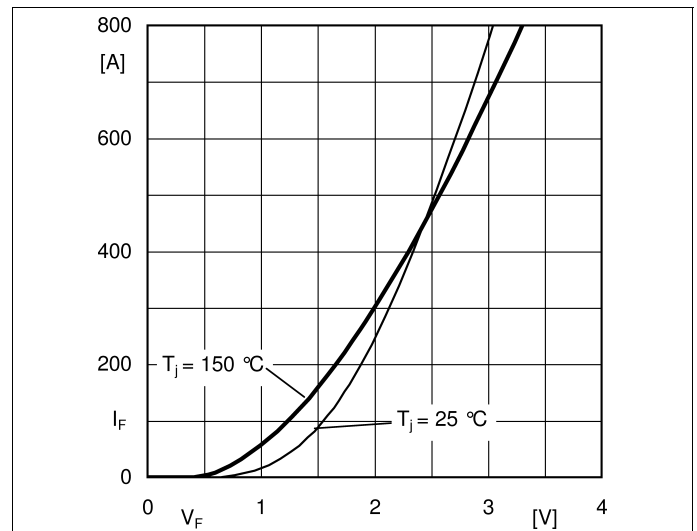
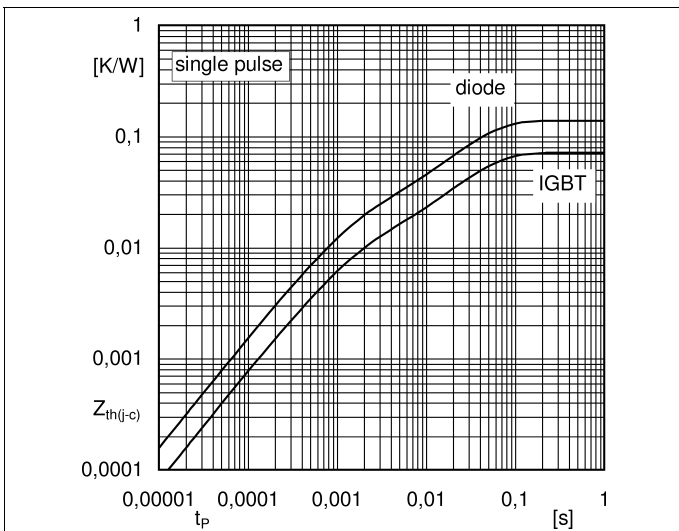
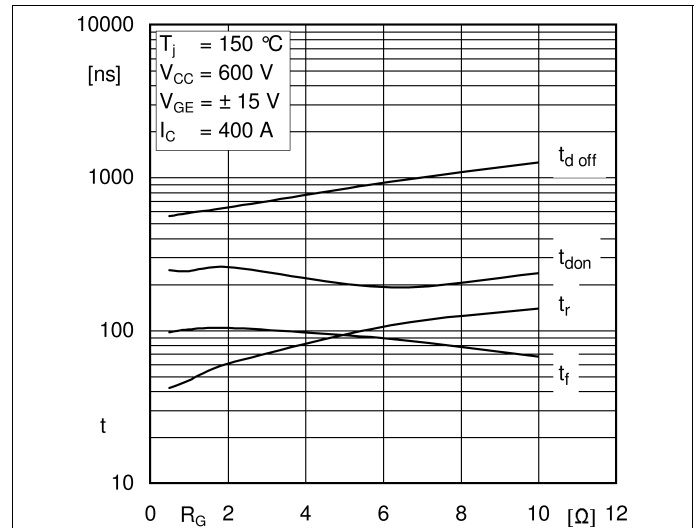
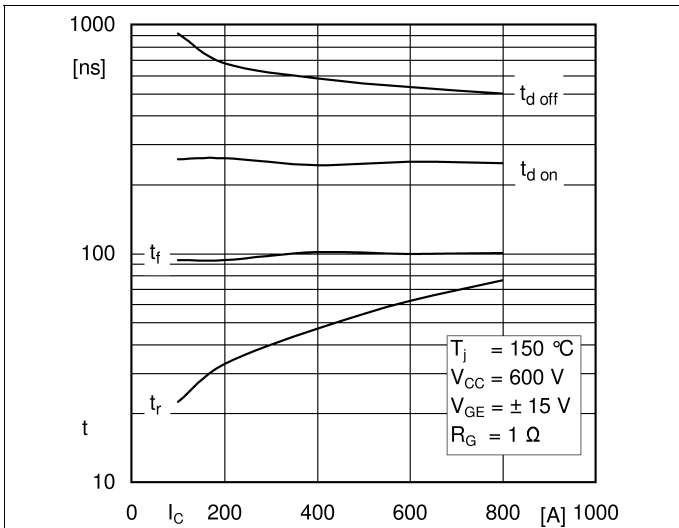
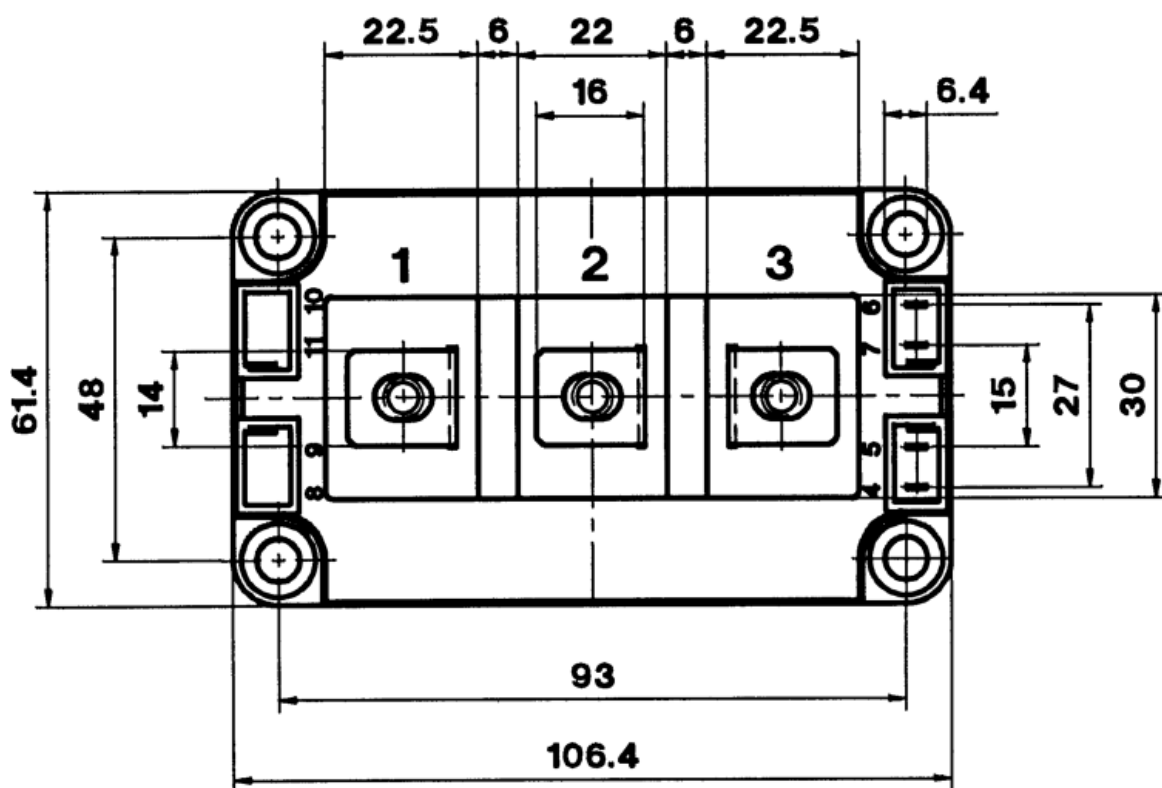
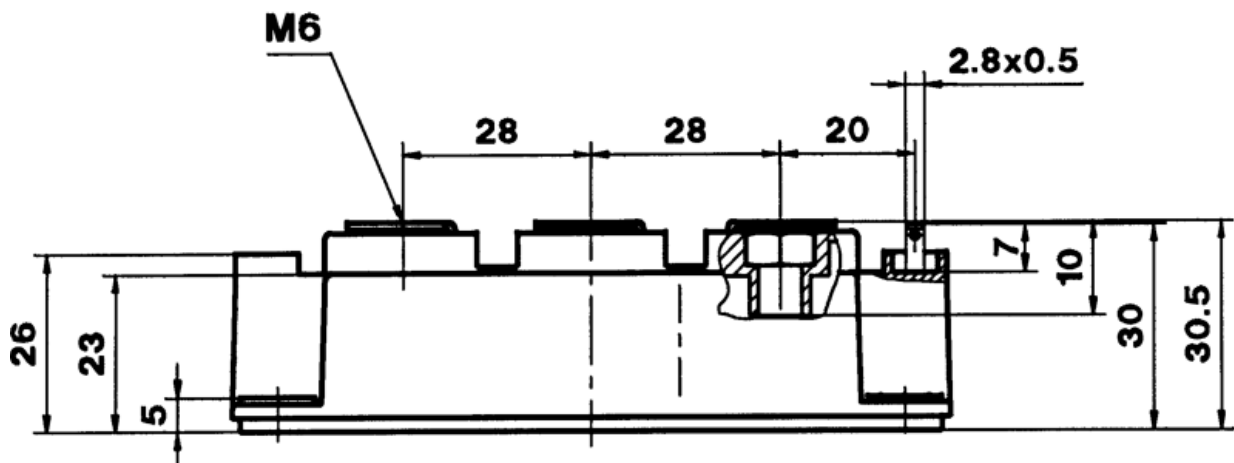
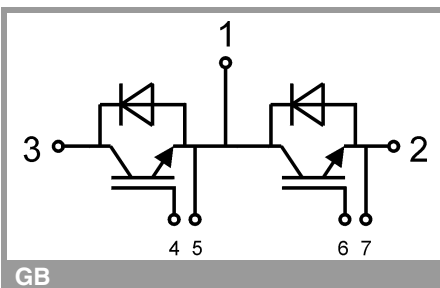


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.